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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re the Application of: KANO, Takashi et al.

Serial No.: 09/941,982

Examiner: MULPURI, Savitri

Group Art Unit: 2812

Filed: August 30, 2001

P.T.O. Confirmation No.: 7536

METHOD OF FORMING NITRIDE-BASED SEMICONDUCTOR LAYER, AND For. METHOD OF MANUFACTURING NITRIDE-BASED SEMICONDUCTOR **DEVICE**

PETITION FOR EXTENSION OF TIME

Commissioner for Patents Washington, D.C. 20231

Date: November 27, 2002

Sir:

Applicants petition the Commissioner for Patents to extend the time for response to the Office Action dated June 28, 2002 for two months from September 28, 2002 to November 28, 2002.

Attached please find a check in the amount of \$400.00 to cover the cost of the extension for a large entity. In the event that any additional fees are due in connection with this paper, please charge our Deposit Account No. 01-2340. Two copies of this paper are enclosed herewith.

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Respectfully submitted,

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